Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	semi adj insulating adj gallium adj nitride adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/25 11:54
S2	3119	semi adj insulating adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 14:02
S3	7784	gallium adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 08:38
S4	79	S2 and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 14:02
S5	0	instrinsic same gallium adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 14:51
S6	2	("20020100916").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/16 15:27
S7	20	intrinsic adj gallium adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 15:27
S8	8	("5686738").URPN.	USPAT	OR	ON	2004/11/16 15:46

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S9	64	("3683240" "3819974"	US-PGPUB;	OR	ON	2004/11/16 16:00
		"3829556" "4144116"	USPAT;			
		"4153905" "4396929"	USOCR	1		
		"4473938" "4476620"				
		"4589015" "4608581"				
		"4615766" "4792467"				
		"4819057" "4819058"				
		"4855249" "4866007"				
		"4897149" "4911102"				
		"4918497" "4946547"				
		"4946548" "4960728"				
		"4966862" "4966867"				
		"4983249" "5005057"				
		"5006908" "5010033"				
		"5015327" "5027168"				
		"5042043" "5063421"				
		"5068204" "5076860"				
		"5093576" "5097298"				
		"5117267" "5119540"				
		"5122845" "5140385"				
		"5173751" "5178911"				
		"5182670" "5192419"				
		"5200022" "5205905"				
		"5210051" "5218216"				
		"5237182" "5243204" "5248631" "5273108"				
		"5248631" "5272108"				
		"5290393" "5298767" "5304830" "5306663"				
		"5304820" "5306662" "5307363" "5313078"				
		"5307363" "5313078" "5323022" "5329141"				
		"5334277" "5338944"	-			
		"5359345" "5385862").PN.				
		•				
S10	93	boule and gallium adj nitride	US-PGPUB;	OR	ON	2004/11/16 16:00
			USPAT;			
			USOCR			
S11	84	(cr or chromium or molydenmum	US-PGPUB;	OR	ON	2005/02/16 08:38
322		or mo or tungsten or w or cu or	USPAT;	J OIX	0.1	2000,02,20 00.50
		copper or zinc or zn or platinum or	USOCR			
		pt) and S10	0000.			
C43		• •	LIC DCDUD	OB	001	2004/11/16 16 02
S12	0	transistion adj metal and S11	US-PGPUB;	OR	ON	2004/11/16 16:02
	:		USPAT;			
			USOCR			
S13	54	dopant and S11	US-PGPUB;	OR	ON	2004/11/16 16:09
		·	USPAT;			
			USOCR			
S14	35	insulating near gallium adj nitride	US-PGPUB;	OR	ON	2004/11/16 16:09
317	33	modiating near gamum auj millue	USPAT;	J.K	UN	2007/11/10 10:09
			USOCR			
			USOCK	L	<u> </u>	<u></u>

S15	11	("5284394" "5344948" "5385862" "5398641" "5464656" "5602418" "5657335" "5786233" "5976412" "6080668" "6291318").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/16 16:12
S16	0	("6544867").URPN.	USPAT	OR	ON	2004/11/16 16:15
S17	92934	transition adj metals	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 19:10
S18	20831	gan or gallium adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 19:10
S19	615	S17 and S18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 19:10
S20	248	insulating and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 19:10
S21	548	(cobalt or co or copper or cu or nickel or ni) and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 19:11
S22	234	S20 and S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 19:11
S23	148	(resistance or resistivity) and S22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 19:12
S24	116	substrate and S23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/16 19:13

S25	3	kyma adj technologies	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 14:31
S26	2	free adj standing and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 14:31
S27	534	(gan or gallium adj nitride) same (co or cobalt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 15:54
S28	28	deep and impurity and S27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 15:54
S29	85	(gan or gallium adj nitride) same (cobalt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 15:54
S30	0	deep and impurity and S29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 15:54
S31	8288	gallium adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 08:38
S32	3755	(cr or chromium or molydenmum or mo or tungsten or w or cu or copper or zinc or zn or platinum or pt or co or cobalt or ni or nickel or fe or iron or mn or manganese) and S31	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/16 08:40
S33	347	(hyvpe or hydride adj vapor adj phase adj epitaxy) and S32	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/16 08:43
S34	39	semi adj insulating and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 08:43

S35		diameter near4 gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/22 11:37
S36	292	diameter same gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/22 11:56
S37	78	free adj standing adj gan or free adj standing adj gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/22 11:58
S38	2863452	diameter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/22 11:59
S39	50	S37 and S38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/22 11:59
S40	2	("6596079").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/22 13:28
S41	437325	large adj area adj gan adj substrate or large adj area adj gan wafer or large adj area adj gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 11:31
S42	1421	iron adj doped or fe adj doped	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 11:31

S43	344	S41 and S42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 11:31
S44	10	("3421952").URPN.	USPAT	OR	ON	2006/01/04 11:42
S45	14	semi adj insulating adj gallium adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 11:42
S46	41	("4144116").URPN.	USPAT	OR	ON	2006/01/04 11:50
S47	243	gan near4 resistivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 11:03
S48	37908	impurity adj concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 11:04
S49	50	S47 and S48	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 11:04
S50	72	semi-insulating adj gan or semi adj insulating adj gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 11:50
S51	718	257/76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/25 12:27
S52	1080	438/479	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/25 12:27